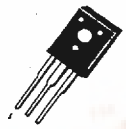
查询2SD882Y供应商 捷多邦，专业PCB打样工厂，24小时加急出货

2SD882/2SD882S NPN Epitaxial Silicon Transistor

AUDIO FREQUENCY POWER AMPLIFIER
LOW SPEED SWITCHING

- Complement to 2SB772

TO-126



1.Emitter 2.Collector 3.Base

ABSOLUTE MAXIMUM RATINGS (Ta = 25 ℃)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	40	V
Collector-Emitter Voltage	V_{CEO}	30	V
Emitter-Bias Voltage	V_{EBO}	5	V
Collector Current (DC)	I_C	3	A
*Collector Current (Pulse)	I_C	7	A
Base Current (DC)	I_B	0.6	A
Collector Dissipation (Ta=25℃)	P_C	10	W
Collector Dissipation (Ta=25℃)	P_C	1	W
Junction Temperature	Tj	150	℃
Storage Temperature	Tstg	-55~150	℃

- PW ≤ 10ms,Duty Cycle ≤ 50%

ELECTRICAL CHARACTERISTICS(Ta=25℃)

Characteristics	Symbol	Test condition	Min	Typ	Min	Unit
Collector Cutoff Current	I_{CBO}	V_{CB}=30V,I_E=0			1	μA
Emitter Cutoff Current	I_{EBO}	V_{EB}=3V,I_C=0			1	μA
*DC Current Gain	h_{FE1}	V_{CE}=2V,I_C=20mA	30	150		
	h_{FE2}	V_{CE}=2V,I_C=1A	60	160	400	
*Collector Emitter Saturation Voltage	$V_{CE(SAT)}$	I_C=2A,I_B=0.2A		0.3	0.5	V
*Base Emitter Saturation Voltage	$V_{BE(SAT)}$	I_C=2A,I_B=0.2A		1.0	2.0	V
Current Gain Bandwidth Product	f_T	V_{CE}=5V,I_C=0.1A		90		MHz
Output Capacitance	Cob	V_{CB}=10V,I_E=0 f=1MHz		45		pF

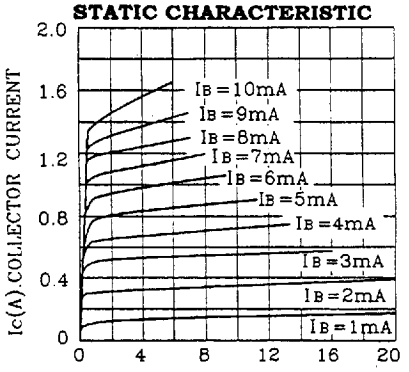
- Pulse Test PW ≤ 350μs,Duty Cycle ≤ 2%

h_{FE}(2) CLASSIFICATION

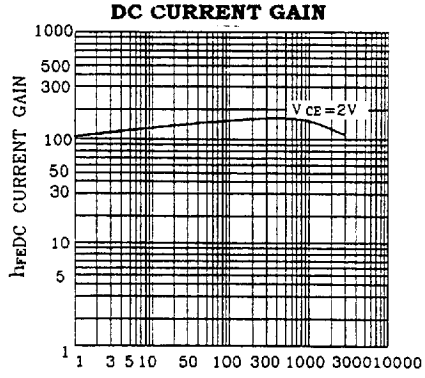
Classification	R	O	Y	G
h_{FE}(2)	60-120	100-200	160-320	200-400

找PDF 维库一下 pdf.dzsc.com

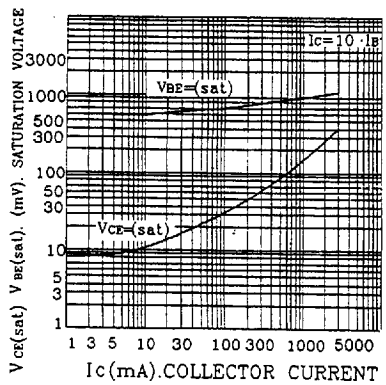
STATIC CHARACTERISTIC



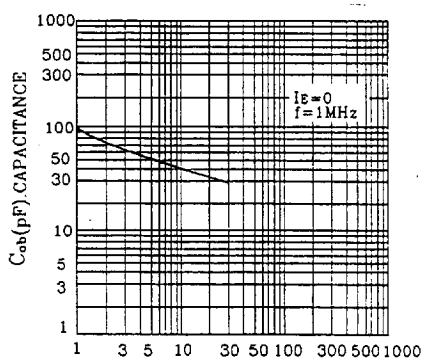
DC CURRENT GAIN



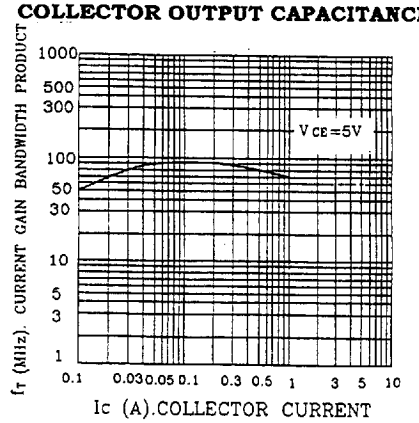
BASE-EMITTER SATURATION VOLTAGE COLLECTOR-EMITTER SATURATION VOLTAGE



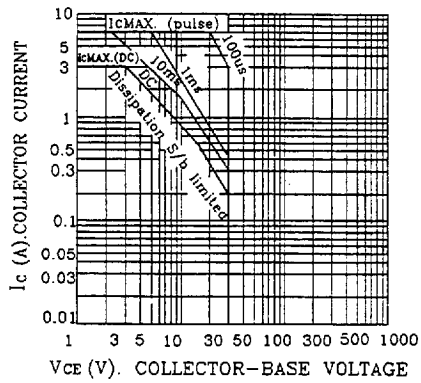
CURRENT GAIN-BANDWIDTH PRODUCT



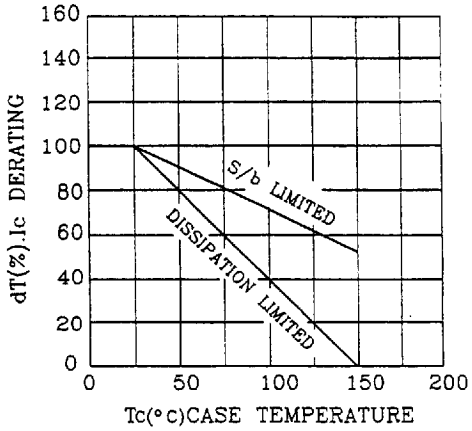
COLLECTOR OUTPUT CAPACITANCE



SAFE OPERATING AREAS



DERATING CURVE OF SAFE OPERATING AREAS



POWER DERATING